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NTE74HCT240 & NTE74HCT244 Integrated Circuit TTL – High Speed CMOS, Octal Buffer/Line Driver/Receiver with 3–State Outputs

Description:

The NTE74HCT240 (Inverting Outputs) and NTE74HCT244 (Non–Inverting Outputs) are 3–STATE buffers in a 20–Lead DIP type package that utilize advanced silicon–gate CMOS technology and are general purpose high speed buffers. They possess high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits achieve speeds comparable to low power Schottky devices, while retaining the low power consumption of CMOS. Both devices are TTL input compatible and have a fanout of 15 LS–TTL equivalent inputs. Each device has two active low enables (1G and 2G), and each enable independently controls 4 buffers.

These devices are intended to interface between TTL and NMOS components and standard CMOS devices and are also plug–in replacements for LS–TTL devices and can be used to reduce power consumption in existing designs.

All inputs are protected from damage due to static discharge by diodes to V_{CC} and GND.

Features:

- TTL Input Compatible
- Typical Propagation Delay: 14ns
- 3–STATE Outputs for Connection to System Buses
- Low Quiescent Current: 80 μ A
- High Output Drive Current: 6mA (min)

Absolute Maximum Ratings: (Note 1, Note 2)

Supply Voltage, V_{CC}	-0.5 to +7.0V
DC Input Voltage, V_{IN}	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage, V_{OUT}	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current, I_{IK}, I_{OK}	$\pm 20mA$
DC Output Current (Per Pin), I_{OUT}	$\pm 35mA$
DC V_{CC} or GND Current (Per Pin), I_{CC}	$\pm 70mA$
Power Dissipation (Note 3), P_D	600mW
Storage Temperature Range, T_{stg}	-65°C to +150°C
Lead Temperature (During Soldering, 10sec), T_L	+260°C

Note 1. Absolute Maximum Ratings are those values beyond which damage to the device may occur.
 Note 2. Unless otherwise specified, all voltages are referenced to GND.
 Note 3. Power Dissipation temperature derating: 12mW/°C from +65°C to +85°C.

Recommended Operating Conditions:

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V_{CC}	4.5	–	5.5	V
DC Input or Output Voltage	V_{IN}, V_{OUT}	0	–	V_{CC}	V
Operating Temperature Range	T_A	–40	–	+85	°C
Input Rise or Fall Times	t_r, t_f	–	–	500	ns

DC Electrical Characteristics: ($V_{CC} = 5V \pm 10\%$ unless otherwise specified)

Parameter	Symbol	Test Conditions	$T_A = +25^\circ\text{C}$		Unit		
			Typ	Guaranteed Limits			
Minimum High Level Input Voltage	V_{IH}		–	2.0	2.0	V	
Maximum Low Level Input Voltage	V_{IL}		–	0.8	0.8	V	
Minimum High Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$ I_{OUT} = 20\mu\text{A}$	V_{CC}	$V_{CC}^{-0.1}$	$V_{CC}^{-0.1}$	V
			$ I_{OUT} = 6.0\text{mA}, V_{CC} = 4.5\text{V}$	4.2	3.98	3.84	V
			$ I_{OUT} = 7.2\text{mA}, V_{CC} = 5.5\text{V}$	5.7	4.98	4.84	V
Maximum Low Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$	$ I_{OUT} = 20\mu\text{A}$	0	0.1	0.1	V
			$ I_{OUT} = 6.0\text{mA}, V_{CC} = 4.5\text{V}$	0.2	0.26	0.33	V
			$ I_{OUT} = 7.2\text{mA}, V_{CC} = 5.5\text{V}$	0.2	0.26	0.33	V
Maximum Input Current	I_{IN}	$V_{IN} = V_{CC}$ or GND, V_{IH} or V_{IL}	–	± 0.05	± 0.5	μA	
Maximum 3–STATE Output Leakage Current	I_{OZ}	$V_{OUT} = V_{CC}$ or GND, $\bar{G} = V_{IH}$, $G = V_{IL}$	–	± 0.25	± 2.5	μA	
Maximum Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0\mu\text{A}$	–	4.0	40	μA	
		$V_{IN} = 2.4\text{V}$ or 0.5V , Note 4	0.6	1.0	1.3	mA	

Note 4. This is measured per input with all other inputs held at V_{CC} or GND.

AC Electrical Characteristics: ($V_{CC} = 5V$, $t_r = t_f = 6\text{ns}$, $T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Typ	Guaranteed Limits	Unit
Maximum Output Propagation Delay	t_{PHL}, t_{PLH}	$C_L = 45\text{pF}$	14	18	ns
Maximum Output Enable Time	t_{PZL}, t_{PZH}	$C_L = 45\text{pF}, R_L = 1\text{k}\Omega$	20	30	ns
Maximum Output Disable Time	t_{PLZ}, t_{PHZ}	$C_L = 5\text{pF}, R_L = 1\text{k}\Omega$	16	25	ns

AC Electrical Characteristics: ($V_{CC} = 5V \pm 10\%$, $t_r = t_f = 6\text{ns}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	$T_A = +25^\circ\text{C}$		Unit		
			Typ	Guaranteed Limits			
Maximum Output Propagation Delay	t_{PHL}, t_{PLH}	$C_L = 50\text{pF}$	14	20	25	ns	
		$C_L = 150\text{pF}$	20	28	35	ns	
Maximum Output Enable Time	t_{PZH}, t_{PZL}	$R_L = 1\text{k}\Omega$	$C_L = 50\text{pF}$	21	30	38	ns
			$C_L = 150\text{pF}$	26	42	53	ns
Maximum Output Disable Time	t_{PHZ}, t_{PLZ}	$R_L = 1\text{k}\Omega, C_L = 50\text{pF}$	16	25	32	ns	
Maximum Output Rise and Fall Time	t_{THL}, t_{TLH}	$C_L = 50\text{pF}$	6	12	15	ns	
Maximum Input Capacitance	C_{IN}		10	15	15	pF	
Maximum Output Capacitance	C_{OUT}		15	20	20	pF	
Power Dissipation Capacitance (Per Buffer, Note 5)	C_{PD}	$\bar{G} = V_{CC}, G = \text{GND}$	5	–	–	pF	
		$\bar{G} = \text{GND}, G = V_{CC}$	90	–	–	pF	

Note 5. C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Truth Tables:

NTE74HCT240:

1G	1A	1Y	2G	2A	2Y
L	L	H	L	L	H
L	H	L	L	H	L
H	L	Z	H	L	Z
H	H	Z	H	H	Z

H = HIGH Level

L = LOW Level

Z = High Impedance

NTE74HCT244:

1G	1A	1Y	2G	2A	2Y
L	L	L	L	L	L
L	H	H	L	H	H
H	L	Z	H	L	Z
H	H	Z	H	H	Z

H = HIGH Level

L = LOW Level

Z = High Impedance

Pin Connection Diagram



